

L Number	Hits	Search Text	DE	Time stamp
1	6	(("6309524") or ("5516412") or ("4304641") or ("6179982") or ("6099712") or ("6176992")).PN.	USPAT	2002/08/23 09:54
3	37810	electropolish or electrochemical	USPAT	2002/08/23 09:55
4	23	(electropolish or electrochemical) and (diffuser) and anode and (disk pad)	USPAT	2002/08/23 10:01
5	872	205/118,157,48,123.ccls.	USPAT	2002/08/23 10:01
6	2468	204/224r,224m,275.1,217,212,282.ccls.	USPAT	2002/08/23 10:02
7	3266	205/118,157,48,123.ccls.	USPAT	2002/08/23 10:02
8	243	204/224r,224m,275.1,217,212,282.ccls.)	USPAT	2002/08/23 10:03
2	37	and (diffuser diaphragm baffle) electropolish and electrochemical	USPAT	2002/08/23 10:54
-	0	156.345.11.ccls.	USPAT	2002/08/14 14:07
-	2602	156/345.\$.ccls.	USPAT	2002/08/14 14:07
-	1375	134/\$.ccls. and ((wet adj etch\$3) dip\$3)	USPAT	2002/08/14 14:08
-	1625	((156/345.\$.ccls. and ((wet adj etch\$3) dip\$3)) (134/\$.ccls. and ((wet adj etch\$3) dip\$3))	USPAT	2002/08/14 14:08
-	1820	furukawa.in.	USPAT	2002/08/14 14:10
-	580	((((156/345.\$.ccls. and ((wet adj etch\$3) dip\$3)) (134/\$.ccls. and ((wet adj etch\$3) dip\$3))) and (cover lid)) (furukawa.in. and (dip (wet adj etch\$3)))	USPAT	2002/08/14 14:10
-	0	furukawa-takahiro.in. and (dip (wet adj etch\$3))	USPAT	2002/08/14 14:10
-	6	furukawa-takahiro.in.	USPAT	2002/08/14 14:11
-	500	((156/345.\$.ccls. and ((wet adj etch\$3) dip\$3)) (134/\$.ccls. and ((wet adj etch\$3) dip\$3))) and (cover lid)	USPAT	2002/08/14 15:02
-	21760	(dip\$3 near5 (process\$3 or coat\$3))	USPAT	2002/08/14 15:03
-	3332	((dip\$3 near5 (process\$3 or coat\$3))) and (semiconductor wafer)	USPAT	2002/08/14 15:04
-	3304	((((dip\$3 near5 (process\$3 or coat\$3))) and (semiconductor wafer)) not ((156/345.\$.ccls. and ((wet adj etch\$3) dip\$3)) (134/\$.ccls. and ((wet adj etch\$3) dip\$3))) and (cover lid))	USPAT	2002/08/14 15:04
-	972	(((((dip\$3 near5 (process\$3 or coat\$3))) and (semiconductor wafer)) not ((156/345.\$.ccls. and ((wet adj etch\$3) dip\$3)) (134/\$.ccls. and ((wet adj etch\$3) dip\$3))) and (cover lid))) and (roof cover lid)	USPAT	2002/08/14 15:40
-	340	(((((dip\$3 near5 (process\$3 or coat\$3))) and (semiconductor wafer)) not ((156/345.\$.ccls. and ((wet adj etch\$3) dip\$3)) (134/\$.ccls. and ((wet adj etch\$3) dip\$3))) and (cover lid))) and (roof cover lid) not (dry plasma)	USPAT	2002/08/20 14:33
-	79	156/345.11.ccls.	USPAT	2002/08/20 14:01
-	80	furukawa.in. and (dip (wet adj etch\$3))	USPAT	2002/08/20 14:08
-	19285	wet near5 etch\$3	USPAT	2002/08/20 14:34
-	16388	(wet near5 etch\$3) and semiconductor	USPAT	2002/08/20 14:34

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